



Welcome to [E-XFL.COM](#)

What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I ² C, LINbus, SIO, SSU, UART/USART
Peripherals	POR, Voltage Detect, WDT
Number of I/O	41
Program Memory Size	48KB (48K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	2.5K x 8
Voltage - Supply (Vcc/Vdd)	2.2V ~ 5.5V
Data Converters	A/D 12x10b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	52-LQFP
Supplier Device Package	52-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21257snfp-v2

1.2 Performance Overview

Table 1.1 outlines the Functions and Specifications for R8C/24 Group and Table 1.2 outlines the Functions and Specifications for R8C/25 Group.

Table 1.1 Functions and Specifications for R8C/24 Group

Item		Specification
CPU	Number of fundamental instructions	89 instructions
	Minimum instruction execution time	50 ns (f(XIN) = 20 MHz, VCC = 3.0 to 5.5 V) 100 ns (f(XIN) = 10 MHz, VCC = 2.7 to 5.5 V) 200 ns (f(XIN) = 5 MHz, VCC = 2.2 to 5.5 V)
	Operating mode	Single-chip
	Address space	1 Mbyte
	Memory capacity	Refer to Table 1.3 Product Information for R8C/24 Group
Peripheral Functions	Ports	I/O ports: 41 pins, Input port: 3 pins
	LED drive ports	I/O ports: 8 pins
	Timers	Timer RA: 8 bits × 1 channel Timer RB: 8 bits × 1 channel (Each timer equipped with 8-bit prescaler) Timer RD: 16 bits × 2 channels (Input capture and output compare circuits) Timer RE: With real-time clock and compare match function
	Serial interfaces	2 channels (UART0, UART1) Clock synchronous serial I/O, UART
	Clock synchronous serial interface	1 channel I ² C bus Interface ⁽¹⁾ Clock synchronous serial I/O with chip select
	LIN module	Hardware LIN: 1 channel (timer RA, UART0)
	A/D converter	10-bit A/D converter: 1 circuit, 12 channels
	Watchdog timer	15 bits × 1 channel (with prescaler) Reset start selectable
	Interrupts	Internal: 11 sources, External: 5 sources, Software: 4 sources, Priority levels: 7 levels
	Clock	Clock generation circuits
		3 circuits • XIN clock generation circuit (with on-chip feedback resistor) • On-chip oscillator (high speed, low speed) High-speed on-chip oscillator has a frequency adjustment function • XCIN clock generation circuit (32 kHz)
		Real-time clock (timer RE)
	Oscillation stop detection function	XIN clock oscillation stop detection function
	Voltage detection circuit	On-chip
	Power-on reset circuit	On-chip
Electrical Characteristics	Supply voltage	VCC = 3.0 to 5.5 V (f(XIN) = 20 MHz) VCC = 2.7 to 5.5 V (f(XIN) = 10 MHz) VCC = 2.2 to 5.5 V (f(XIN) = 5 MHz)
	Current consumption	Typ. 10 mA (VCC = 5.0 V, f(XIN) = 20 MHz) Typ. 6 mA (VCC = 3.0 V, f(XIN) = 10 MHz) Typ. 2.0 μA (VCC = 3.0 V, wait mode (f(XCIN) = 32 kHz)) Typ. 0.7 μA (VCC = 3.0 V, stop mode)
Flash Memory	Programming and erasure voltage	VCC = 2.7 to 5.5 V
	Programming and erasure endurance	100 times
Operating Ambient Temperature		-20 to 85°C (N version)
		-40 to 85°C (D version) ⁽²⁾
		-20 to 105°C (Y version) ⁽³⁾
Package		52-pin molded-plastic LQFP
		64-pin molded-plastic FLGA

NOTES:

1. I²C bus is a trademark of Koninklijke Philips Electronics N. V.
2. Specify the D version if D version functions are to be used.
3. Please contact Renesas Technology sales offices for the Y version.

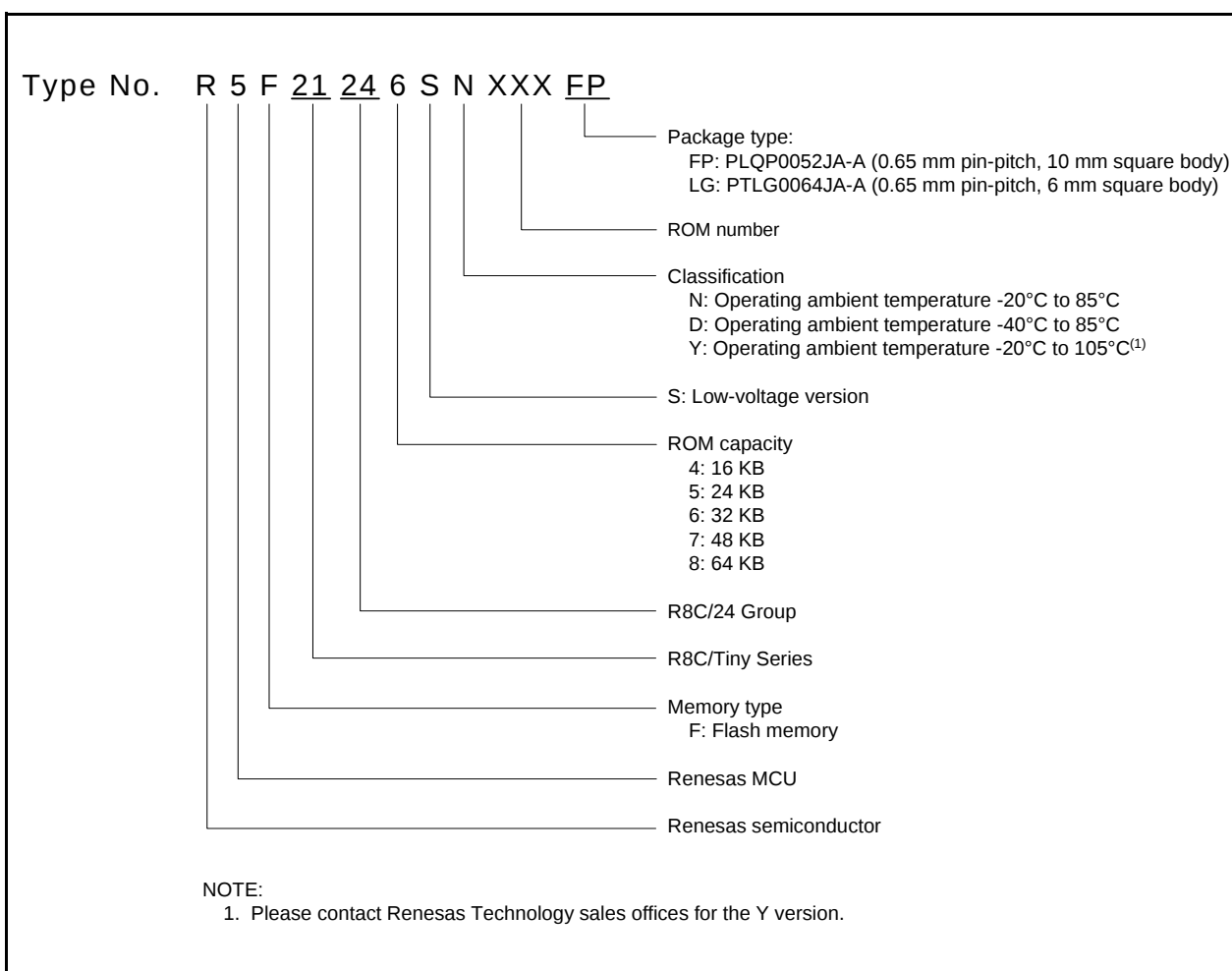


Figure 1.2 Type Number, Memory Size, and Package of R8C/24 Group

Table 1.4 Product Information for R8C/25 Group

Current of Feb. 2008

Type No.	ROM Capacity		RAM Capacity	Package Type	Remarks
	Program ROM	Data flash			
R5F21254SNFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0052JA-A	N version Blank product
R5F21255SNFP	24 Kbytes	1 Kbyte × 2	2 Kbytes	PLQP0052JA-A	
R5F21256SNFP	32 Kbytes	1 Kbyte × 2	2 Kbytes	PLQP0052JA-A	
R5F21257SNFP	48 Kbytes	1 Kbyte × 2	2.5 Kbytes	PLQP0052JA-A	
R5F21258SNFP	64 Kbytes	1 Kbyte × 2	3 Kbytes	PLQP0052JA-A	
R5F21254SNLG	16 Kbytes	1 Kbyte × 2	1 Kbyte	PTLG0064JA-A	
R5F21256SNLG	32 Kbytes	1 Kbyte × 2	2 Kbytes	PTLG0064JA-A	D version Blank product
R5F21254SDFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0052JA-A	
R5F21255SDFP	24 Kbytes	1 Kbyte × 2	2 Kbytes	PLQP0052JA-A	
R5F21256SDFP	32 Kbytes	1 Kbyte × 2	2 Kbytes	PLQP0052JA-A	
R5F21257SDFP	48 Kbytes	1 Kbyte × 2	2.5 Kbytes	PLQP0052JA-A	
R5F21258SDFP	64 Kbytes	1 Kbyte × 2	3 Kbytes	PLQP0052JA-A	
R5F21254SNXXXFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0052JA-A	N version Factory programming product ⁽¹⁾
R5F21255SNXXXFP	24 Kbytes	1 Kbyte × 2	2 Kbytes	PLQP0052JA-A	
R5F21256SNXXXFP	32 Kbytes	1 Kbyte × 2	2 Kbytes	PLQP0052JA-A	
R5F21257SNXXXFP	48 Kbytes	1 Kbyte × 2	2.5 Kbytes	PLQP0052JA-A	
R5F21258SNXXXFP	64 Kbytes	1 Kbyte × 2	3 Kbytes	PLQP0052JA-A	
R5F21254SNXXXLG	16 Kbytes	1 Kbyte × 2	1 Kbyte	PTLG0064JA-A	
R5F21256SNXXXLG	32 Kbytes	1 Kbyte × 2	2 Kbytes	PTLG0064JA-A	D version Factory programming product ⁽¹⁾
R5F21254SDXXXFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0052JA-A	
R5F21255SDXXXFP	24 Kbytes	1 Kbyte × 2	2 Kbytes	PLQP0052JA-A	
R5F21256SDXXXFP	32 Kbytes	1 Kbyte × 2	2 Kbytes	PLQP0052JA-A	
R5F21257SDXXXFP	48 Kbytes	1 Kbyte × 2	2.5 Kbytes	PLQP0052JA-A	
R5F21258SDXXXFP	64 Kbytes	1 Kbyte × 2	3 Kbytes	PLQP0052JA-A	

NOTE:

1. The user ROM is programmed before shipment.

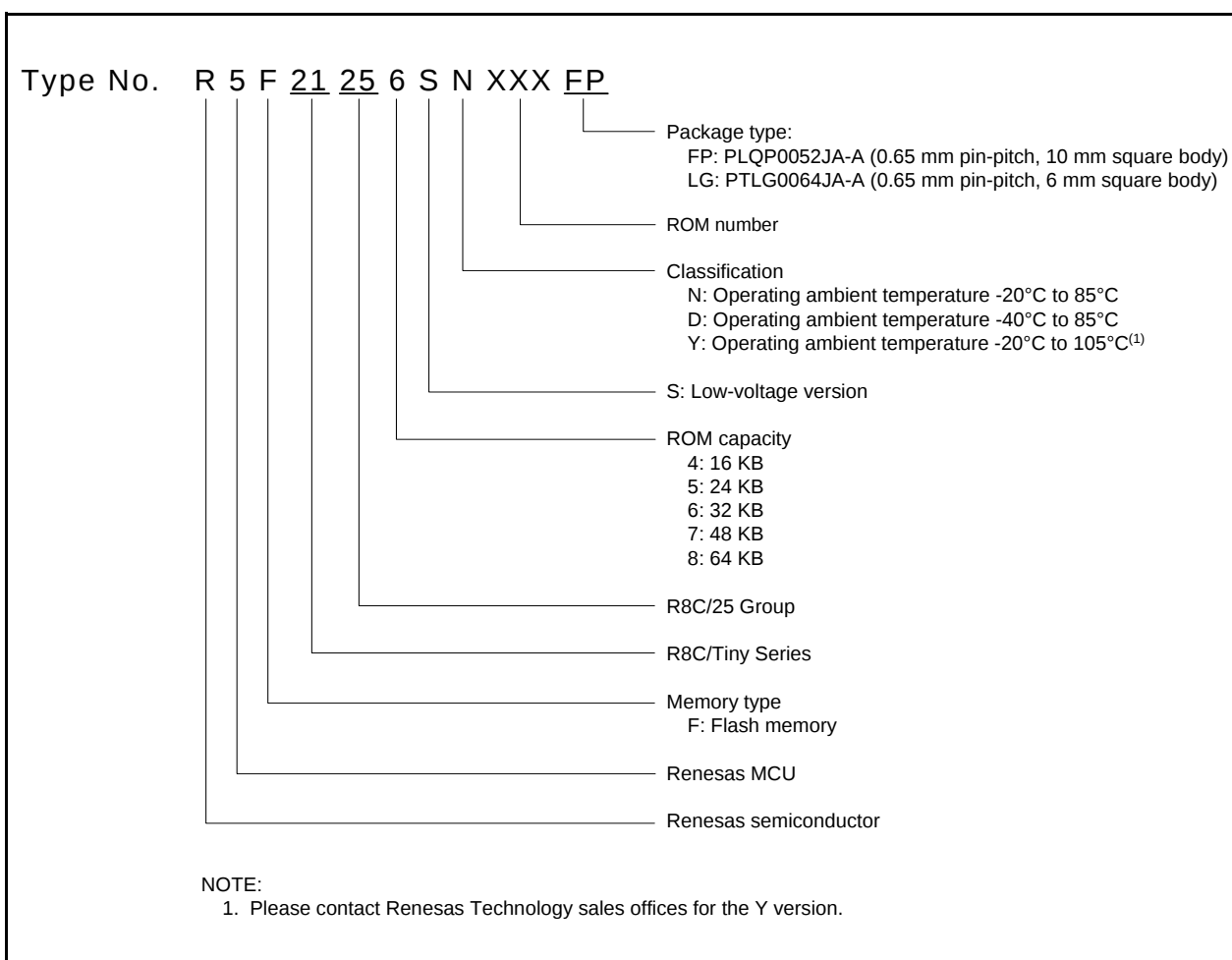


Figure 1.3 Type Number, Memory Size, and Package of R8C/25 Group

1.5 Pin Assignments

Figure 1.4 shows PLQP0052JA-A Package Pin Assignments (Top View). Figure 1.5 shows PTLG0064JA-A Package Pin Assignments.

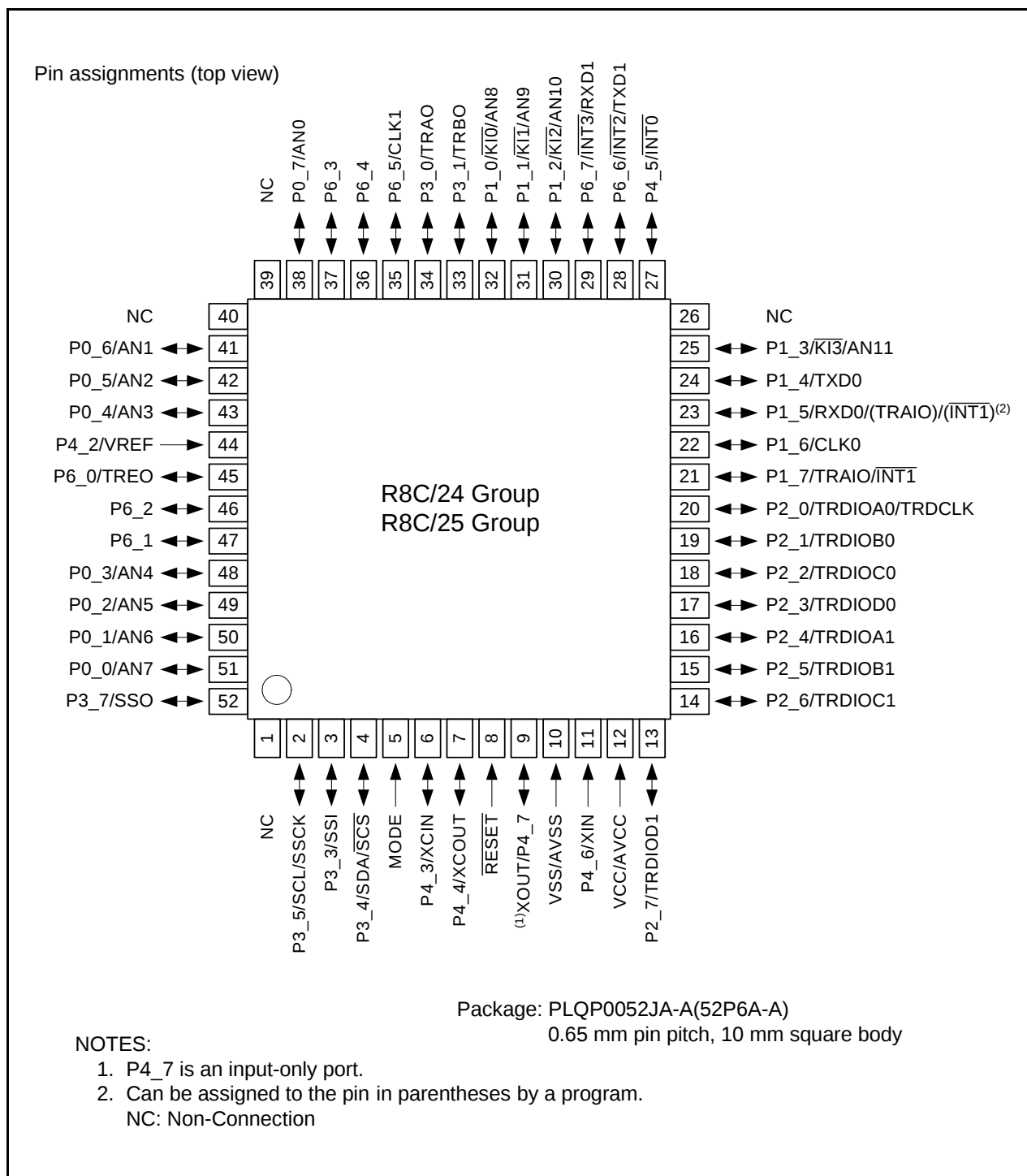


Figure 1.4 PLQP0052JA-A Package Pin Assignments (Top View)

1.6 Pin Functions

Table 1.5 lists Pin Functions.

Table 1.5 Pin Functions

Type	Symbol	I/O Type	Description
Power supply input	VCC, VSS	I	Apply 2.2 V to 5.5 V to the VCC pin. Apply 0 V to the VSS pin.
Analog power supply input	AVCC, AVSS	I	Power supply for the A/D converter. Connect a capacitor between AVCC and AVSS.
Reset input	$\overline{\text{RESET}}$	I	Input "L" on this pin resets the MCU.
MODE	MODE	I	Connect this pin to VCC via a resistor.
XIN clock input	XIN	I	These pins are provided for XIN clock generation circuit I/O. Connect a ceramic resonator or a crystal oscillator between the XIN and XOUT pins. To use an external clock, input it to the XIN pin and leave the XOUT pin open.
XIN clock output	XOUT	O	
XCIN clock input	XCIN	I	These pins are provided for XCIN clock generation circuit I/O. Connect a crystal oscillator between the XCIN and XCOU pins. To use an external clock, input it to the XCIN pin and leave the XCOU pin open.
XCIN clock output	XCOU	O	
$\overline{\text{INT}}$ interrupt input	$\overline{\text{INT0}}$ to $\overline{\text{INT3}}$	I	$\overline{\text{INT}}$ interrupt input pins. $\overline{\text{INT0}}$ is timer RD input pin. $\overline{\text{INT1}}$ is timer RA input pin.
Key input interrupt	$\overline{\text{KI0}}$ to $\overline{\text{KI3}}$	I	Key input interrupt input pins
Timer RA	TRAIO	I/O	Timer RA I/O pin
	TRAO	O	Timer RA output pin
Timer RB	TRBO	O	Timer RB output pin
Timer RD	TRDIOA0, TRDIOA1, TRDIOB0, TRDIOB1, TRDIOC0, TRDIOC1, TRDIOD0, TRDIOD1	I/O	Timer RD I/O ports
	TRDCLK	I	External clock input pin
Timer RE	TREO	O	Divided clock output pin
Serial interface	CLK0, CLK1	I/O	Transfer clock I/O pin
	RXD0, RXD1	I	Serial data input pins
	TXD0, TXD1	O	Serial data output pins
I ² C bus interface	SCL	I/O	Clock I/O pin
	SDA	I/O	Data I/O pin
Clock synchronous serial I/O with chip select	SSI	I/O	Data I/O pin
	$\overline{\text{SCS}}$	I/O	Chip-select signal I/O pin
	SSCK	I/O	Clock I/O pin
	SSO	I/O	Data I/O pin
Reference voltage input	VREF	I	Reference voltage input pin to A/D converter
A/D converter	AN0 to AN11	I	Analog input pins to A/D converter
I/O port	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0, P3_1, P3_3 to P3_5, P3_7, P4_3 to P4_5, P6_0 to P6_7	I/O	CMOS I/O ports. Each port has an I/O select direction register, allowing each pin in the port to be directed for input or output individually. Any port set to input can be set to use a pull-up resistor or not by a program. P2_0 to P2_7 also function as LED drive ports.
Input port	P4_2, P4_6, P4_7	I	Input-only ports

I: Input O: Output I/O: Input and output

Table 1.6 Pin Name Information by Pin Number

Pin Number	Control Pin	Port	I/O Pin Functions for of Peripheral Modules					
			Interrupt	Timer	Serial Interface	Clock Synchronous Serial I/O with Chip Select	I ² C bus Interface	A/D Converter
2		P3_5				SSCK	SCL	
3		P3_3				SSI		
4		P3_4				SCS	SDA	
5	MODE							
6	XCIN	P4_3						
7	XCOUT	P4_4						
8	RESET							
9	XOUT	P4_7						
10	VSS/AVSS							
11	XIN	P4_6						
12	VCC/AVCC							
13		P2_7		TRDIOD1				
14		P2_6		TRDIOC1				
15		P2_5		TRDIOB1				
16		P2_4		TRDIOA1				
17		P2_3		TRDIOD0				
18		P2_2		TRDIOC0				
19		P2_1		TRDIOB0				
20		P2_0		TRDIOA0/TRDCLK				
21		P1_7	INT1	TRAIO				
22		P1_6			CLK0			
23		P1_5	(INT1) ⁽¹⁾	(TRAIO) ⁽¹⁾	RXD0			
24		P1_4			TXD0			
25		P1_3	KI3					AN11
27		P4_5	INT0	INT0				
28		P6_6	INT2		TXD1			
29		P6_7	INT3		RXD1			
30		P1_2	KI2					AN10
31		P1_1	KI1					AN9
32		P1_0	KI0					AN8
33		P3_1		TRBO				
34		P3_0		TRA0				
35		P6_5			CLK1			
36		P6_4						
37		P6_3						
38		P0_7						AN0
41		P0_6						AN1
42		P0_5						AN2
43		P0_4						AN3
44	VREF	P4_2						
45		P6_0		TRE0				
46		P6_2						
47		P6_1						
48		P0_3						AN4
49		P0_2						AN5
50		P0_1						AN6
51		P0_0						AN7
52		P3_7				SSO		

NOTE:

1. Can be assigned to the pin in parentheses by a program.

2. Central Processing Unit (CPU)

Figure 2.1 shows the CPU Registers. The CPU contains 13 registers. R0, R1, R2, R3, A0, A1, and FB configure a register bank. There are two sets of register bank.

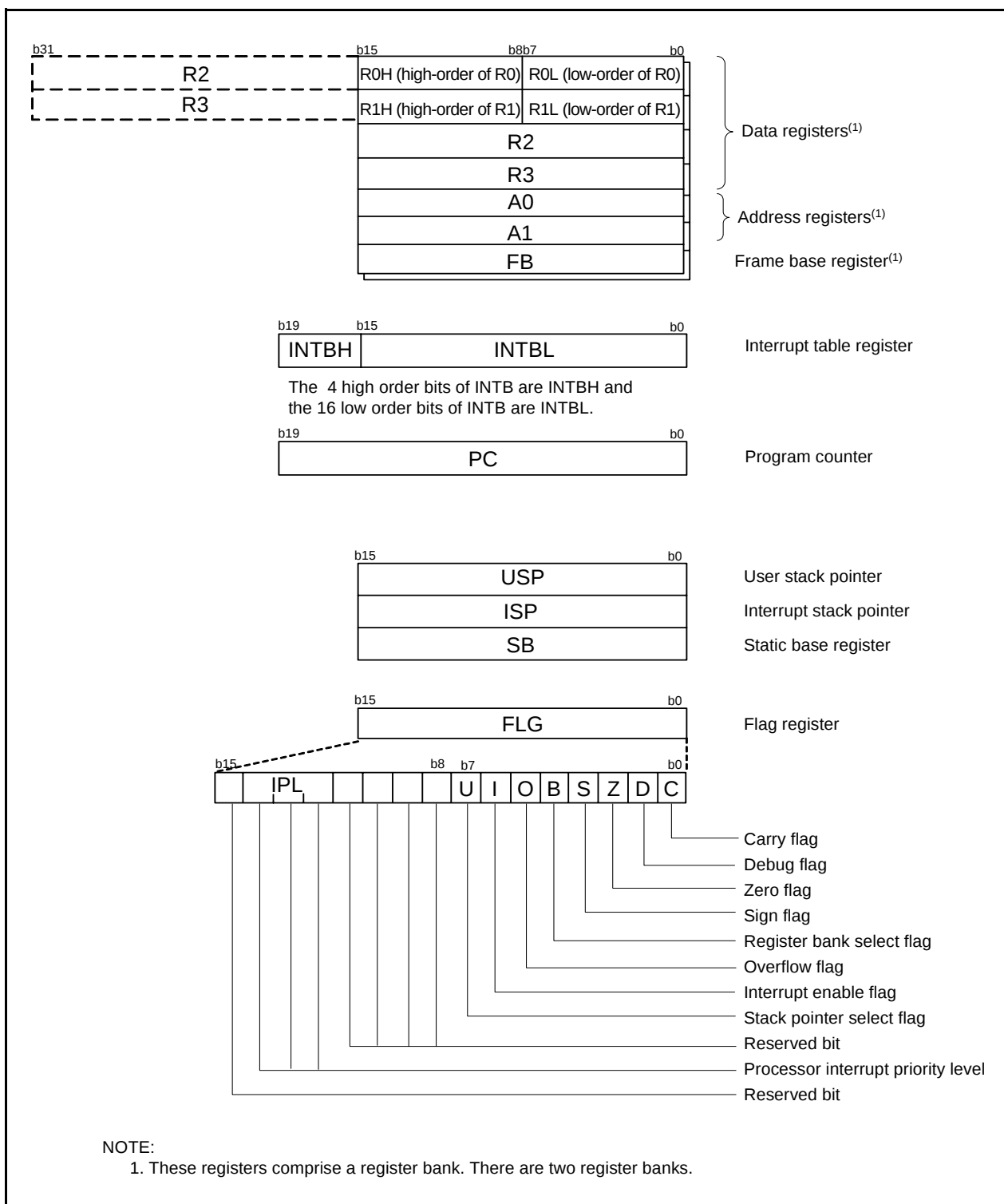


Figure 2.1 CPU Registers

Table 4.5 SFR Information (5)⁽¹⁾

Address	Register	Symbol	After reset
0100h	Timer RA Control Register	TRACR	00h
0101h	Timer RA I/O Control Register	TRAIOC	00h
0102h	Timer RA Mode Register	TRAMR	00h
0103h	Timer RA Prescaler Register	TRAPRE	FFh
0104h	Timer RA Register	TRA	FFh
0105h			
0106h	LIN Control Register	LINCR	00h
0107h	LIN Status Register	LINST	00h
0108h	Timer RB Control Register	TRBCR	00h
0109h	Timer RB One-Shot Control Register	TRBOCR	00h
010Ah	Timer RB I/O Control Register	TRBIOC	00h
010Bh	Timer RB Mode Register	TRBMR	00h
010Ch	Timer RB Prescaler Register	TRBPRES	FFh
010Dh	Timer RB Secondary Register	TRBSC	FFh
010Eh	Timer RB Primary Register	TRBPR	FFh
010Fh			
0110h			
0111h			
0112h			
0113h			
0114h			
0115h			
0116h			
0117h			
0118h	Timer RE Second Data Register / Counter Data Register	TRESEC	00h
0119h	Timer RE Minute Data Register / Compare Data Register	TREMIN	00h
011Ah	Timer RE Hour Data Register	TREHR	00h
011Bh	Timer RE Day of Week Data Register	TREWK	00h
011Ch	Timer RE Control Register 1	TRECR1	00h
011Dh	Timer RE Control Register 2	TRECR2	00h
011Eh	Timer RE Count Source Select Register	TRECSR	00001000b
011Fh			
0120h			
0121h			
0122h			
0123h			
0124h			
0125h			
0126h			
0127h			
0128h			
0129h			
012Ah			
012Bh			
012Ch			
012Dh			
012Eh			
012Fh			
0130h			
0131h			
0132h			
0133h			
0134h			
0135h			
0136h			
0137h	Timer RD Start Register	TRDSTR	11111100b
0138h	Timer RD Mode Register	TRDMR	00001110b
0139h	Timer RD PWM Mode Register	TRDPMR	10001000b
013Ah	Timer RD Function Control Register	TRDFCR	10000000b
013Bh	Timer RD Output Master Enable Register 1	TRDOER1	FFh
013Ch	Timer RD Output Master Enable Register 2	TRDOER2	01111111b
013Dh	Timer RD Output Control Register	TRDOCR	00h
013Eh	Timer RD Digital Filter Function Select Register 0	TRDDF0	00h
013Fh	Timer RD Digital Filter Function Select Register 1	TRDDF1	00h

X: Undefined

NOTE:

1. The blank regions are reserved. Do not access locations in these regions.

5. Electrical Characteristics

The electrical characteristics of N version ($T_{opr} = -20$ to 85°C) and D version ($T_{opr} = -40$ to 85°C) are listed below.

Please contact Renesas Technology sales offices for the electrical characteristics in the Y version ($T_{opr} = -20$ to 105°C).

Table 5.1 Absolute Maximum Ratings

Symbol	Parameter	Condition	Rated Value	Unit
V_{CC}/AV_{CC}	Supply voltage		-0.3 to 6.5	V
V_I	Input voltage		-0.3 to $V_{CC} + 0.3$	V
V_O	Output voltage		-0.3 to $V_{CC} + 0.3$	V
P_d	Power dissipation	$T_{opr} = 25^{\circ}\text{C}$	500 ⁽¹⁾	mW
T_{opr}	Operating ambient temperature		-20 to 85 (N version) / -40 to 85 (D version)	$^{\circ}\text{C}$
T_{stg}	Storage temperature		-65 to 150	$^{\circ}\text{C}$

NOTE:

1. 300 mW for the PTLG0064JA-A package.

Table 5.3 A/D Converter Characteristics

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
—	Resolution		$V_{ref} = AV_{CC}$	—	—	10	Bit
—	Absolute accuracy	10-bit mode	$\phi_{AD} = 10 \text{ MHz}, V_{ref} = AV_{CC} = 5.0 \text{ V}$	—	—	± 3	LSB
		8-bit mode	$\phi_{AD} = 10 \text{ MHz}, V_{ref} = AV_{CC} = 5.0 \text{ V}$	—	—	± 2	LSB
		10-bit mode	$\phi_{AD} = 10 \text{ MHz}, V_{ref} = AV_{CC} = 3.3 \text{ V}$	—	—	± 5	LSB
		8-bit mode	$\phi_{AD} = 10 \text{ MHz}, V_{ref} = AV_{CC} = 3.3 \text{ V}$	—	—	± 2	LSB
		10-bit mode	$\phi_{AD} = 5 \text{ MHz}, V_{ref} = AV_{CC} = 2.2 \text{ V}$	—	—	± 5	LSB
		8-bit mode	$\phi_{AD} = 5 \text{ MHz}, V_{ref} = AV_{CC} = 2.2 \text{ V}$	—	—	± 2	LSB
R_{ladder}	Resistor ladder		$V_{ref} = AV_{CC}$	10	—	40	$k\Omega$
t_{conv}	Conversion time	10-bit mode	$\phi_{AD} = 10 \text{ MHz}, V_{ref} = AV_{CC} = 5.0 \text{ V}$	3.3	—	—	μs
		8-bit mode	$\phi_{AD} = 10 \text{ MHz}, V_{ref} = AV_{CC} = 5.0 \text{ V}$	2.8	—	—	μs
V_{ref}	Reference voltage			2.2	—	AV_{CC}	V
V_{IA}	Analog input voltage ⁽²⁾			0	—	AV_{CC}	V
—	A/D operating clock frequency	Without sample and hold	$V_{ref} = AV_{CC} = 2.7 \text{ to } 5.5 \text{ V}$	0.25	—	10	MHz
		With sample and hold	$V_{ref} = AV_{CC} = 2.7 \text{ to } 5.5 \text{ V}$	1	—	10	MHz
		Without sample and hold	$V_{ref} = AV_{CC} = 2.2 \text{ to } 5.5 \text{ V}$	0.25	—	5	MHz
		With sample and hold	$V_{ref} = AV_{CC} = 2.2 \text{ to } 5.5 \text{ V}$	1	—	5	MHz

NOTES:

1. $AV_{CC} = 2.2 \text{ to } 5.5 \text{ V}$ at $T_{opr} = -20 \text{ to } 85^\circ\text{C}$ (N version) / $-40 \text{ to } 85^\circ\text{C}$ (D version), unless otherwise specified.
2. When the analog input voltage is over the reference voltage, the A/D conversion result will be 3FFh in 10-bit mode and FFh in 8-bit mode.

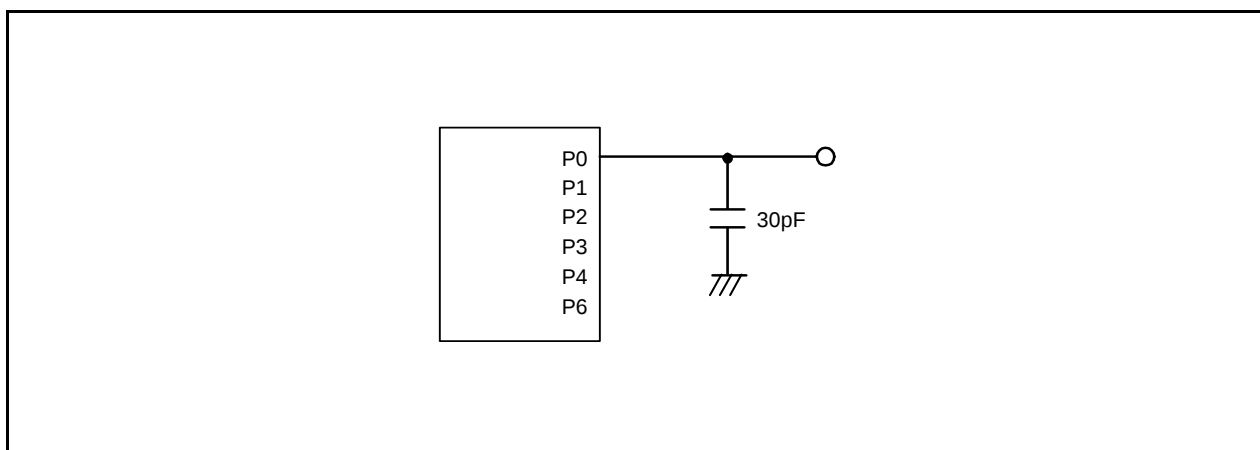
**Figure 5.1 Ports P0 to P4, P6 Timing Measurement Circuit**

Table 5.4 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance ⁽²⁾	R8C/24 Group	100 ⁽³⁾	–	–	times
		R8C/25 Group	1,000 ⁽³⁾	–	–	times
–	Byte program time		–	50	400	μs
–	Block erase time		–	0.4	9	s
t _d (SR-SUS)	Time delay from suspend request until suspend		–	–	97+CPU clock × 6 cycles	μs
–	Interval from erase start/restart until following suspend request		650	–	–	μs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3+CPU clock × 4 cycles	μs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.2	–	5.5	V
–	Program, erase temperature		0	–	60	°C
–	Data hold time ⁽⁷⁾	Ambient temperature = 55°C	20	–	–	year

NOTES:

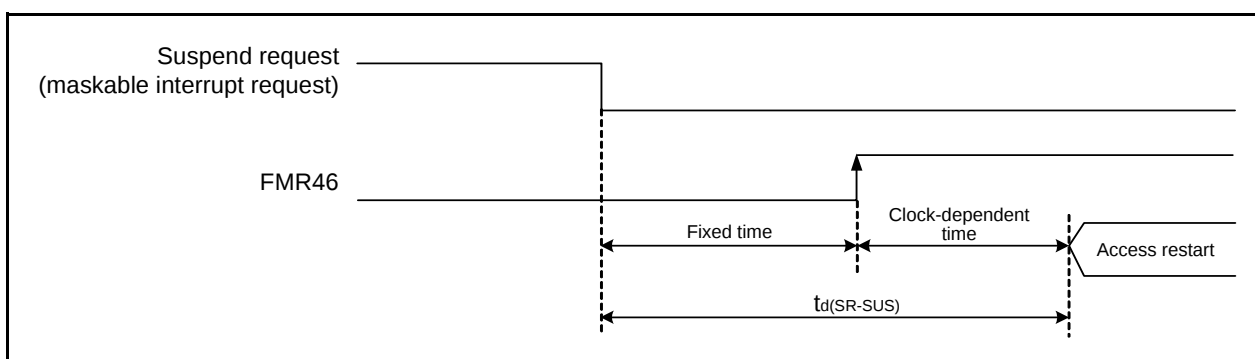
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = 0 to 60°C, unless otherwise specified.
2. Definition of programming/erasure endurance
The programming and erasure endurance is defined on a per-block basis.
If the programming and erasure endurance is n (n = 100 or 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erase count of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.5 Flash Memory (Data flash Block A, Block B) Electrical Characteristics⁽⁴⁾

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
—	Program/erase endurance ⁽²⁾		10,000 ⁽³⁾	—	—	times
—	Byte program time (program/erase endurance ≤ 1,000 times)		—	50	400	μs
—	Byte program time (program/erase endurance > 1,000 times)		—	65	—	μs
—	Block erase time (program/erase endurance ≤ 1,000 times)		—	0.2	9	s
—	Block erase time (program/erase endurance > 1,000 times)		—	0.3	—	s
t _d (SR-SUS)	Time delay from suspend request until suspend		—	—	97+CPU clock × 6 cycles	μs
—	Interval from erase start/restart until following suspend request		650	—	—	μs
—	Interval from program start/restart until following suspend request		0	—	—	ns
—	Time from suspend until program/erase restart		—	—	3+CPU clock × 4 cycles	μs
—	Program, erase voltage		2.7	—	5.5	V
—	Read voltage		2.2	—	5.5	V
—	Program, erase temperature		-20 ⁽⁸⁾	—	85	°C
—	Data hold time ⁽⁹⁾	Ambient temperature = 55 °C	20	—	—	year

NOTES:

1. V_{CC} = 2.7 to 5.5 V at T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
2. Definition of programming/erasure endurance
The programming and erasure endurance is defined on a per-block basis.
If the programming and erasure endurance is n (n = 100 or 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. Standard of block A and block B when program and erase endurance exceeds 1,000 times. Byte program time to 1,000 times is the same as that in program ROM.
5. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erase count of each block and limit the number of erase operations to a certain number.
6. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
7. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
8. -40°C for D version.
9. The data hold time includes time that the power supply is off or the clock is not supplied.

**Figure 5.2 Time delay until Suspend****Table 5.6 Voltage Detection 0 Circuit Electrical Characteristics**

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V _{det0}	Voltage detection level		2.2	2.3	2.4	V
—	Voltage detection circuit self power consumption	VCA25 = 1, V _{CC} = 5.0 V	—	0.9	—	μA
t _{d(E-A)}	Waiting time until voltage detection circuit operation starts ⁽²⁾		—	—	300	μs
V _{ccmin}	MCU operating voltage minimum value		2.2	—	—	V

NOTES:

1. The measurement condition is V_{CC} = 2.2 to 5.5 V and T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version).
2. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA25 bit in the VCA2 register to 0.

Table 5.7 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V _{det1}	Voltage detection level		2.70	2.85	3.00	V
—	Voltage monitor 1 interrupt request generation time ⁽²⁾		—	40	—	μs
—	Voltage detection circuit self power consumption	VCA26 = 1, V _{CC} = 5.0 V	—	0.6	—	μA
t _{d(E-A)}	Waiting time until voltage detection circuit operation starts ⁽³⁾		—	—	100	μs

NOTES:

1. The measurement condition is V_{CC} = 2.2 to 5.5 V and T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version).
2. Time until the voltage monitor 1 interrupt request is generated after the voltage passes V_{det1}.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.

Table 5.8 Voltage Detection 2 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V _{det2}	Voltage detection level		3.3	3.6	3.9	V
—	Voltage monitor 2 interrupt request generation time ⁽²⁾		—	40	—	μs
—	Voltage detection circuit self power consumption	VCA27 = 1, V _{CC} = 5.0 V	—	0.6	—	μA
t _{d(E-A)}	Waiting time until voltage detection circuit operation starts ⁽³⁾		—	—	100	μs

NOTES:

1. The measurement condition is V_{CC} = 2.2 to 5.5 V and T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version).
2. Time until the voltage monitor 2 interrupt request is generated after the voltage passes V_{det2}.
3. Necessary time until the voltage detection circuit operates after setting to 1 again after setting the VCA27 bit in the VCA2 register to 0.

Table 5.14 Timing Requirements of I²C bus Interface⁽¹⁾

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
t _{SCL}	SCL input cycle time		12t _{CYC} + 600 ⁽²⁾	–	–	ns
t _{SCLH}	SCL input “H” width		3t _{CYC} + 300 ⁽²⁾	–	–	ns
t _{SCLL}	SCL input “L” width		5t _{CYC} + 500 ⁽²⁾	–	–	ns
t _{sf}	SCL, SDA input fall time		–	–	300	ns
t _{SP}	SCL, SDA input spike pulse rejection time		–	–	1t _{CYC} ⁽²⁾	ns
t _{BUF}	SDA input bus-free time		5t _{CYC} ⁽²⁾	–	–	ns
t _{STAH}	Start condition input hold time		3t _{CYC} ⁽²⁾	–	–	ns
t _{STAS}	Retransmit start condition input setup time		3t _{CYC} ⁽²⁾	–	–	ns
t _{STOP}	Stop condition input setup time		3t _{CYC} ⁽²⁾	–	–	ns
t _{SDAS}	Data input setup time		1t _{CYC} + 20 ⁽²⁾	–	–	ns
t _{SDAH}	Data input hold time		0	–	–	ns

NOTES:

1. V_{CC} = 2.2 to 5.5 V, V_{SS} = 0 V and T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
2. 1t_{CYC} = 1/f₁(s)

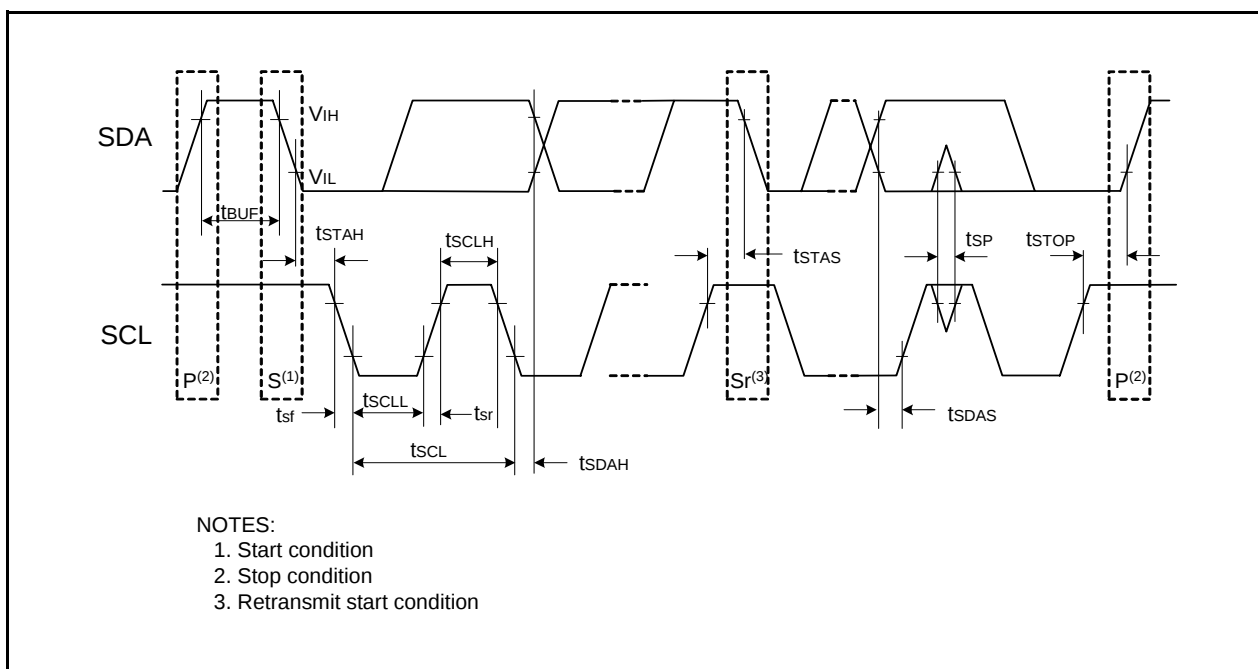
**Figure 5.7 I/O Timing of I²C bus Interface**

Table 5.28 Electrical Characteristics (5) [V_{CC} = 2.2 V]

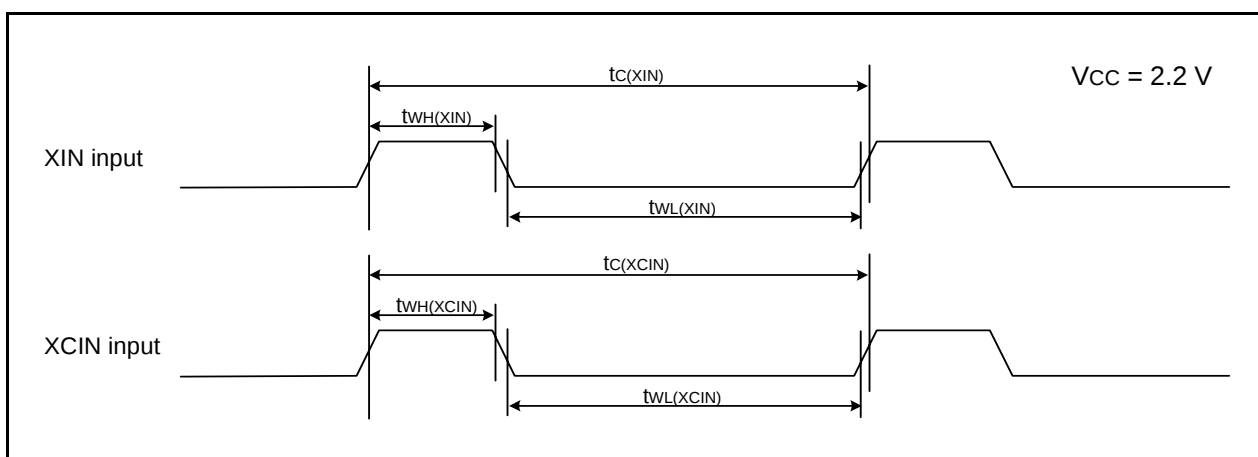
Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V _{OH}	Output "H" voltage	Except P2_0 to P2_7, XOUT	I _{OH} = -1 mA		V _{CC} - 0.5	—	V _{CC}	V
		P2_0 to P2_7	Drive capacity HIGH	I _{OH} = -2 mA	V _{CC} - 0.5	—	V _{CC}	V
			Drive capacity LOW	I _{OH} = -1 mA	V _{CC} - 0.5	—	V _{CC}	V
		XOUT	Drive capacity HIGH	I _{OH} = -0.1 mA	V _{CC} - 0.5	—	V _{CC}	V
			Drive capacity LOW	I _{OH} = -50 μA	V _{CC} - 0.5	—	V _{CC}	V
V _{OL}	Output "L" voltage	Except P2_0 to P2_7, XOUT	I _{OL} = 1 mA		—	—	0.5	V
		P2_0 to P2_7	Drive capacity HIGH	I _{OL} = 2 mA	—	—	0.5	V
			Drive capacity LOW	I _{OL} = 1 mA	—	—	0.5	V
		XOUT	Drive capacity HIGH	I _{OL} = 0.1 mA	—	—	0.5	V
			Drive capacity LOW	I _{OL} = 50 μA	—	—	0.5	V
V _{T+} -V _{T-}	Hysteresis	$\overline{\text{INT0}}, \overline{\text{INT1}}, \overline{\text{INT2}}, \overline{\text{INT3}}, \text{KI0}, \text{KI1}, \text{KI2}, \text{KI3}, \text{TRAIO}, \text{RXD0}, \text{RXD1}, \text{CLK0}, \text{CLK1}, \text{SSI}, \text{SCL}, \text{SDA}, \text{SSO}$			0.05	0.3	—	V
		$\overline{\text{RESET}}$			0.05	0.15	—	V
I _{IH}	Input "H" current		V _I = 2.2 V		—	—	4.0	μA
I _{IL}	Input "L" current		V _I = 0 V		—	—	-4.0	μA
R _{PULLUP}	Pull-up resistance		V _I = 0 V		100	200	600	kΩ
R _{FXIN}	Feedback resistance	XIN			—	5	—	MΩ
R _{FXCIN}	Feedback resistance	XCIN			—	35	—	MΩ
V _{RAM}	RAM hold voltage		During stop mode		1.8	—	—	V

NOTE:

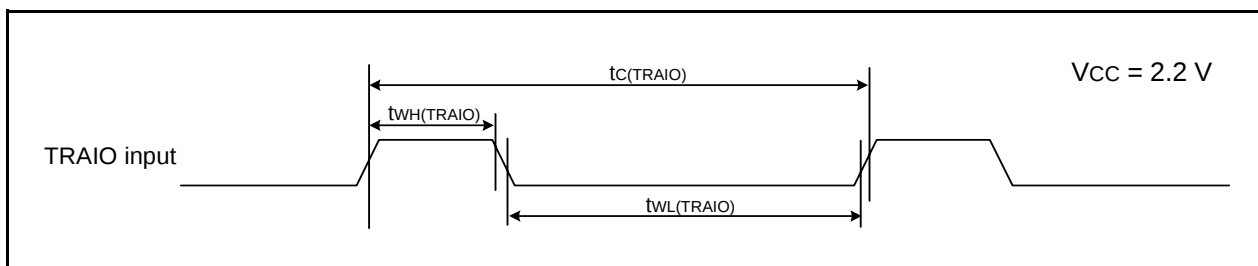
- V_{CC} = 2.2 V at T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), f(XIN) = 5 MHz, unless otherwise specified.

Timing requirements**(Unless Otherwise Specified: $V_{CC} = 2.2\text{ V}$, $V_{SS} = 0\text{ V}$ at $T_{opr} = 25^{\circ}\text{C}$) [$V_{CC} = 2.2\text{ V}$]****Table 5.30 XIN Input, XCIN Input**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XIN)}$	XIN input cycle time	200	–	ns
$t_{WH(XIN)}$	XIN input “H” width	90	–	ns
$t_{WL(XIN)}$	XIN input “L” width	90	–	ns
$t_{c(XCIN)}$	XCIN input cycle time	14	–	μs
$t_{WH(XCIN)}$	XCIN input “H” width	7	–	μs
$t_{WL(XCIN)}$	XCIN input “L” width	7	–	μs

**Figure 5.16 XIN Input and XCIN Input Timing Diagram when $V_{CC} = 2.2\text{ V}$** **Table 5.31 TRAIO Input**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	500	–	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	200	–	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	200	–	ns

**Figure 5.17 TRAIO Input Timing Diagram when $V_{CC} = 2.2\text{ V}$**

REVISION HISTORY	R8C/24 Group, R8C/25 Group Datasheet
------------------	--------------------------------------

Rev.	Date	Description	
		Page	Summary
0.01	Sep 17, 2004	-	First Edition issued
0.02	Dec 10, 2004	All pages 2, 3 4 5, 6 7 8 9 15 16 19	Part Number revised. R8C/26 → R8C/24, R8C/27 → R8C/25 Table 1.1 R8C/24 Group Performance, Table 1.2 R8C/25 Group Performance - Serial Interface: I²C Bus Interface and Chip-select clock synchronous (SSU) added. - LIN Module added. - Interrupt: Internal factors revised; 10 → 11 - Note on Operating Ambient Temperature added. Figure 1.1 Block Diagram - LIN Module added. - Chip-select clock synchronous (SSU) is added to I²C Bus Interface. Table 1.3 Product Information of R8C/24 Group, Table 1.4 Product Information of R8C/25 Group Date and Development state revised. Figure 1.4 Pin Assignment P3_5/SCL → P3_5/SCL/SSCK, P3_3 → P3_3/SSI, P3_4/SDA → P3_4/SDA/SCS, P3_7 → P3_7/SSO, VSS/AVSS → VSS, XIN/P4_6 → P4_6/XIN, VCC/AVSS → VCC 12pin P1_7/TRAO/INT1 to 22pin P1_0/KIO/AN8 → 20pin P1_7/TRAO/INT1 to 30pin P1_0/KIO/AN8 Table 1.5 Pin Description - Analog Power Supply Input eliminated. - SSU added. Table 1.6 Pin Name Information by Pin Number added. Table 4.1 SFR Information (1) - 0031h: Voltage Detection Register 1 → Voltage Detection <u>A</u> Register 1 - 0032h: Voltage Detection Register 1 → Voltage Detection <u>A</u> Register 2 01000001b → 00100001b (Note 4) - 0036h: "(3), 01000001b (4)" eliminated. - 0038h: Voltage Monitor 0 Control Register (2), VW0C, 00001000b (3), 01000001b (4) added. Table 4.2 SFR Information (2) - 0048h: Timer RD0 Interrupt Control Register, RD0IC, XXXXX000b added. - 0049h: Timer RD Interrupt Control Register, RDIC → Timer RD1 Interrupt Control Register, RD1IC - 004Fh: IIC Interrupt Control Register, IIC → IIC/SSU Interrupt Control Register, IIC2IC Table 4.5 SFR Information (3) - 0106h: LIN Control Register, LINCR, 00h added. - 0107h: LIN Status Register, LINST, 00h added.

REVISION HISTORY

R8C/24 Group, R8C/25 Group Datasheet

Rev.	Date	Description	
		Page	Summary
0.10	Feb 24, 2005	1 to 3 5, 6	Pin type changed: 48-pin(under consideration) → 52-pin.
		5 to 7	Package type revised: 48-pin LQFP(under consideration) → PLQP0052JA-A
		8	Table 1.5 TCLK added, VREF revised.
		9	Table 1.6 revised.
		13, 14	Figures 3.1 and 3.2 part number revised.
		15	Tabel 4.1 revised: - 000Fh: 000XXXXXb → 00011111b - 0023h: FR0 → FRA0 - 0024h: FR1 → FRA1 - 0025h: FR2 → FRA2 - 0031h: Voltage Detection A Register 1, VC1 → Voltage Detection Register 1, VCA1 - 0032h: Voltage Detection A Register 2, VC2 → Voltage Detection Register 2, VCA2
		17	Tabel 4.3 Register name and the value after reset at 00B8h to 00BFh revised; NOTE2 added.
		19	Tabel 4.5 revised: - 0107h: LINSR → LINST - 0137h to 013Fh: Register symbol revised
		20	Tabel 4.6 revised: - 0140h to 015Fh: Register symbol revised - 0158h, 0159h: Timer RD General Register → Timer RD General Register A1
0.20	Mar 8, 2005	2, 3 8	Tables 1.1, 1.2 and 1.5 revised: "main clock" → "XIN clock"; "sub clock" → "XCIN clock"
		15	- 0023h to 0025h: 40MHz On-Chip Oscillator Control Register → High-Speed On-Chip Oscillator Control Register
0.30	Sep 01, 2005	2, 3	Table 1.1 R8C/24 Group Performance, Table 1.2 R8C/25 Group Performance • Serial Interface revised: - Serial Interface: 2 channels Clock synchronous serial I/O, UART - Clock Synchronous Serial Interface: 1 channel I ² C bus Interface ⁽¹⁾ , Clock synchronous serial I/O with chip select
		4	Figure 1.1 Block Diagram • UART or Clock Synchronous Serial Interface: "(8 bits × 1 channel)" → "(8 bits × 2 channels)" revised • UART (8 bits × 1 channel) deleted
		5, 6	Table 1.3 Product Information of R8C/24 Group, Table 1.4 Product Information of R8C/25 Group "Flash Memory Version" → "N Version" revised

REVISION HISTORY	R8C/24 Group, R8C/25 Group Datasheet
------------------	--------------------------------------

Rev.	Date	Description	
		Page	Summary
0.30	Sep 01, 2005	19	Tabel 4.5 SFR Information(5) revised: • 0118h : Timer RE Second Data Register/Counter Register → Timer RE Second Data Register/Counter Data Register
		20	Tabel 4.6 SFR Information(6) revised: • 0145h POCR0 → TRDPOCR0 • 0146h, 0147h TRDCNT0 → TRD0 • 0148h, 0149h GRA0 → TRDGRA0 • 014Ah, 014Bh GRB0 → TRDGRB0 • 014Ch, 014Dh GRC0 → TRDGRC0 • 014Eh, 014Fh GRD0 → TRDGRD0 • 0155h POCR1 → TRDPOCR1 • 0156h, 0157h TRDCNT1 → TRD1 • 0158h, 0159h GRA1 → TRDGRA1 • 015Ah, 015Bh GRB1 → TRDGRB1 • 015Ch, 015Dh GRC1 → TRDGRC1 • 015Eh, 015Fh GRD1 → TRDGRD1
		21	Tabel 4.7 SFR Information(7) revised: • 01B5h: 01000101b → 1000000Xb • 01B7h: XX000001b → 00000001b • FFFFh: (Note 2) added
		22 to 44	5. Electrical Characteristics added
0.40	Jan 24, 2006	all pages	• “Preliminary” deleted • Symbol name “TRDMDR” → “TRDMR”, “SSUAIC” → “SSUIC”, and “IIC2AIC” → “IICIC” revised • Pin name “TCLK” → “TRDCLK” revised
		2	Table 1.1 Functions and Specifications for R8C/24 Group revised
		3	Table 1.2 Functions and Specifications for R8C/25 Group revised
		4	Figure 1.1 Block Diagram; “Peripheral Functions” added, “System Clock Generation” → “System Clock Generator” revised
		5	Table 1.3 Product Information for R8C/24 Group revised
		6	Table 1.4 Product Information for R8C/25 Group revised
		7	Figure 1.4 Pin Assignments (Top View) “TCLK” → “TRDCLK” revised
		8	Table 1.5 Pin Functions “TCLK” → “TRDCLK” revised
		9	Table 1.6 Pin Name Information by Pin Number; “TCLK” → “TRDCLK” revised
		10	Figure 2.1 CPU Registers; “Reserved Area” → “Reserved Bit” revised
		12	2.8.10 Reserved Area; “Reserved Area” → “Reserved bit” revised
		13	Figure 3.1 Memory Map of R8C/24 Group; “Program area” → “program ROM” revised
		14	3.2 R8C/25 Group, Figure 3.2 Memory Map of R8C/25 Group; “Data area” → “data flash”, “Program area” → “program ROM” revised